Product data sheet

1. General description

Ultrafast, dual common cathode, epitaxial rectifier diode in a TO220F plastic package.

2. Features and benefits

- Fast switching
- Low thermal resistance
- · Soft recovery characteristics
- Isolated package
- · Low forward voltage drop
- High thermal cycling performance

3. Applications

- Output rectifiers in high frequency switched-mode power supplies.
- Discontinuous Current Mode (DCM) Power Factor Correction (PFC)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit
Absolute	maximum rating					
V_{RRM}	repetitive peak reverse voltage		600			V
I _{O(AV)}	average output current	δ = 0.5 ; T _h ≤ 44 °C; square-wave pulse; both diodes conducting	20			А
I _{FRM}	repetitive peak forward current	$δ = 0.5$; $t_p = 25 \mu s$; $T_h \le 44 °C$; square-wave pulse; per diode	20			А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode				А
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode			А	
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics		'	'		
V _F	forward voltage	I _F = 10 A; T _j = 25 °C; per diode; <u>Fig. 6</u>	-	1.07	1.36	V
		I _F = 10 A; T _j = 150 °C; per diode; <u>Fig. 6</u>	-	0.92	1.16	V
Dynamic	characteristics					
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ per diode}; Fig. 7$	-	50	60	ns

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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode	mb	
2	K	cathode		A1
3	A2	anode		K
mb	n.c.	mounting base; isolated		`` sym125

6. Ordering information

Table 3. Ordering information

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BYV34X-600	TO-220F	BYV34X-600,127	Tube	50	SOT186A	14-Nov-2013

7. Marking

Table 4. Marking codes

Type number	Marking codes			
	Assembly factory: d			
BYV34X-600	BYV34X 600 PJdxxxx xx	BYV34X 600 PJAxxxx xx		

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		600	V
V_{RWM}	crest working reverse voltage		600	V
V_R	reverse voltage	DC	600	V
I _{O(AV)}	average output current	δ = 0.5 ; T _h ≤ 44 °C; square-wave pulse; both diodes conducting	20	А
I _{FRM}	repetitive peak forward current	$δ = 0.5$; $t_p = 25 \mu s$; $T_h \le 44 °C$; square-wave pulse; per diode	20	А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode	120	А
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode	132	А
T _{stg}	storage temperature		-40 to 150	°C
T _j	junction temperature		150	°C

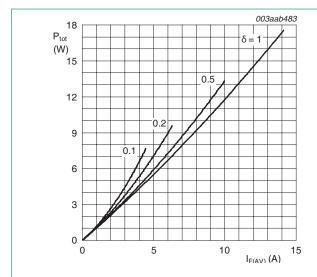
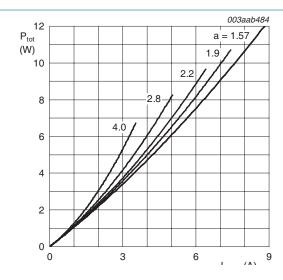


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode

 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$



a = form factor = $I_{F(RMS)}/I_{F(AV)}$

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values; per diode

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)} thermal resistance from junction to heatsink		with heatsink compound; per diode; Fig. 3	-	-	5	K/W
	with heatsink compound; both diodes conducting	-	-	4	K/W	
		without heatsink compound; per diode	-	-	7	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	55	-	K/W

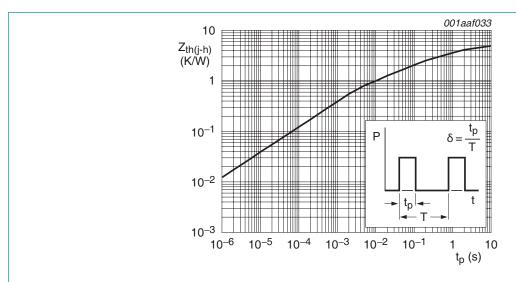


Fig. 3. Transient thermal impedance from junction to heatsink as a function of pulse duration

10. Isolation characteristics

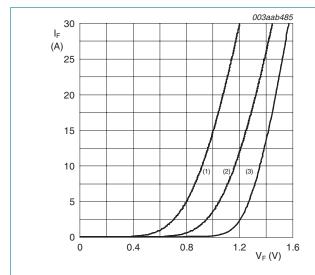
Table 7. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	from cathode to external heatsink	-	10	-	pF

11. Characteristics

Table 8. Characteristics

Table 0. Of	iaracteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V_{F}	forward current	$I_F = 10 \text{ A}; T_j = 25 ^{\circ}\text{C}; \text{ per diode}; Fig. 4$	-	1.07	1.36	V
		I _F = 10 A; T _j = 150 °C; per diode; <u>Fig. 4</u>	-	0.92	1.16	V
I _R	reverse current	$V_R = 600 \text{ V}; T_j = 25 ^{\circ}\text{C}; \text{ per diode}$	-	10	50	μA
		$V_R = 600 \text{ V}; T_j = 100 ^{\circ}\text{C}; \text{ per diode}$	-	0.2	0.6	mA
Dynamic	characteristics					
Q _r	reverse charge	$I_F = 2 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 20 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ per diode}; \frac{\text{Fig. 5}}{\text{C}}$	-	40	70	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ per diode}; \frac{\text{Fig. 5}}{100 \text{ Fig. 5}}$	-	50	60	ns
I _{RM}	peak reverse recovery current	$I_F = 10 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 150 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; per diode; Fig. 5$	-	3	5	А
V_{FR}	forward recovery voltage	$I_F = 10 \text{ A}$; $dI_F/dt = 10 \text{ A}/\mu\text{s}$; $T_j = 25 \text{ °C}$; per diode; Fig. 6	-	3.2	-	V



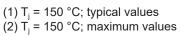


Fig. 4. Forward current as a function of forward voltage; per diode

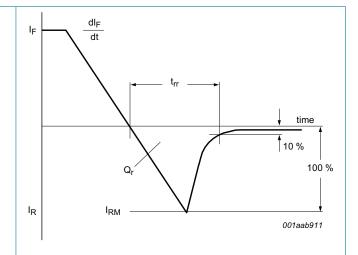
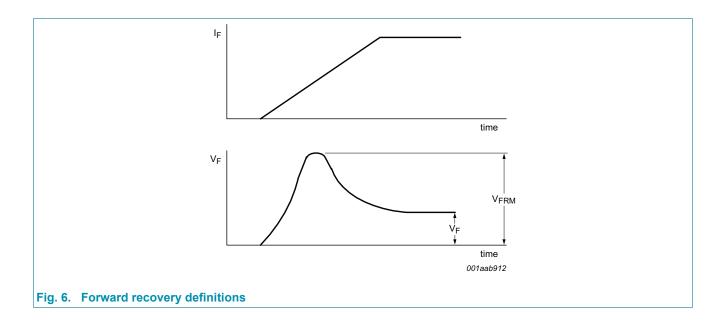


Fig. 5. Reverse recovery definitions; ramp recovery

⁽³⁾ $T_i = 25$ °C; maximum values

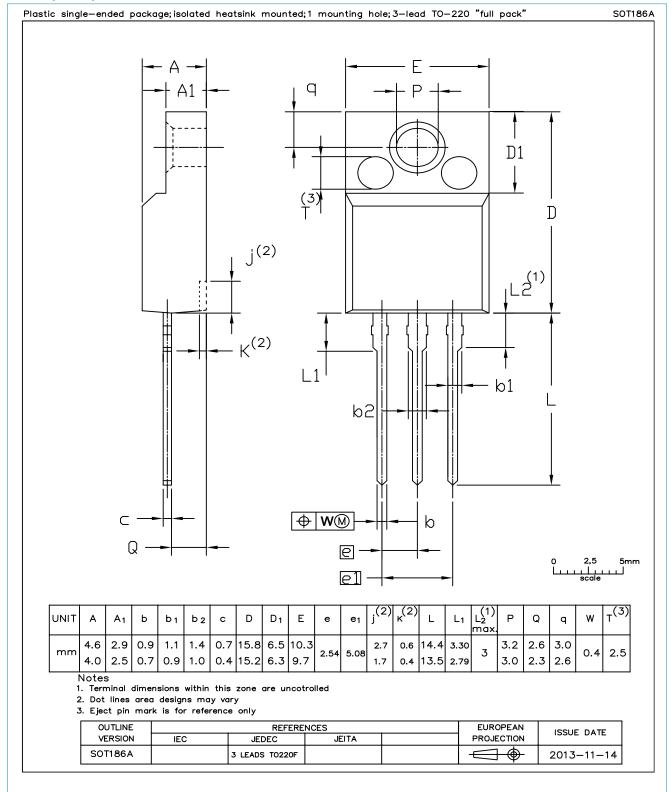
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12. Package outline

Assembly factory: d & A



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13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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